

EEC 210 Fall 2005 Midterm

Rajeevan Amirtharajah
Dept. of Electrical and Computer Engineering
University of California, Davis

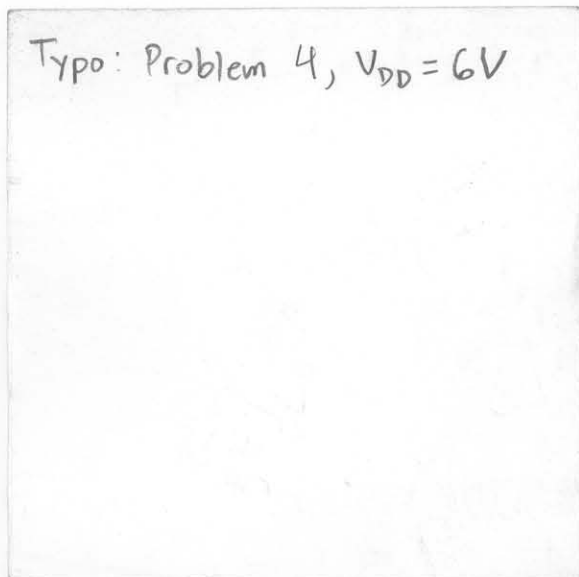
November 15, 2005

Name: *Solutions*

Instructions: This test consists of 4 problems and 13 pages, including the cover sheet. Please make sure that you have all of them. This is an open-book, open-notes test. State any assumptions you make and show complete work to receive credit. The time limit is 80 minutes. The problems are weighted as shown below

Grading:

Problem	Maximum	Score
1	12	
2	16	
3	10	
4	12	
Total	50	



1 CMOS Inverter Amplifier

Figure 1 shows a CMOS inverter biased as a linear amplifier. For this problem, use the transistor parameters in Table 1.

Parameter	NMOS	PMOS
V_t	1 V	-1 V
L_d	0	0
X_d	0	0
k'	$300 \mu\text{A}/\text{V}^2$	$100 \mu\text{A}/\text{V}^2$
γ	0	0
W/L	2	6
λ	0.1 V^{-1}	0.1 V^{-1}

Table 1: Problem 1 Transistor Parameters.

Problem 1.1 (3 points) Assume $V_I = 1.5 \text{ V}$. For what range of V_O will the circuit best act as an amplifier? What is the output voltage swing?

Want M1 + M2 in saturation:

$$V_{GS1} = V_I = 1.5 \text{ V}, V_{OV1} = 0.5 \text{ V} \Rightarrow V_{out} \geq 0.5 \text{ V}$$

$$V_{GS2} = V_{DD} - V_I = 1.5 \text{ V}, V_{OV2} = 0.5 \text{ V} \Rightarrow V_{out} \leq 2.5 \text{ V}$$

$$0.5 \text{ V} \leq V_{out} \leq 2.5 \text{ V}$$

$$\begin{aligned} \text{Output Swing} &= 2 \text{ V as amplifier} \\ &= 3 \text{ V } (0 \leq V_O \leq V_{DD}) \text{ for output levels} \end{aligned}$$

Problem 1.2 (2 points) Find the power dissipation assuming the bias conditions in Problem 1.1.

$$I_{D1} = I_{D2} = \frac{k'_n}{2} \left(\frac{W}{L}\right)_n (V_I - V_{tn})^2 = \frac{300 \mu\text{A}/\text{V}^2}{2} (2) (1.5 \text{ V} - 1)^2$$

$$= 75 \mu\text{A} \quad (86.2 \mu\text{A} \text{ if } \lambda = 0.1 \text{ V}^{-1})$$

$$P = I_{D1} V_{DD} = 225 \mu\text{W}$$

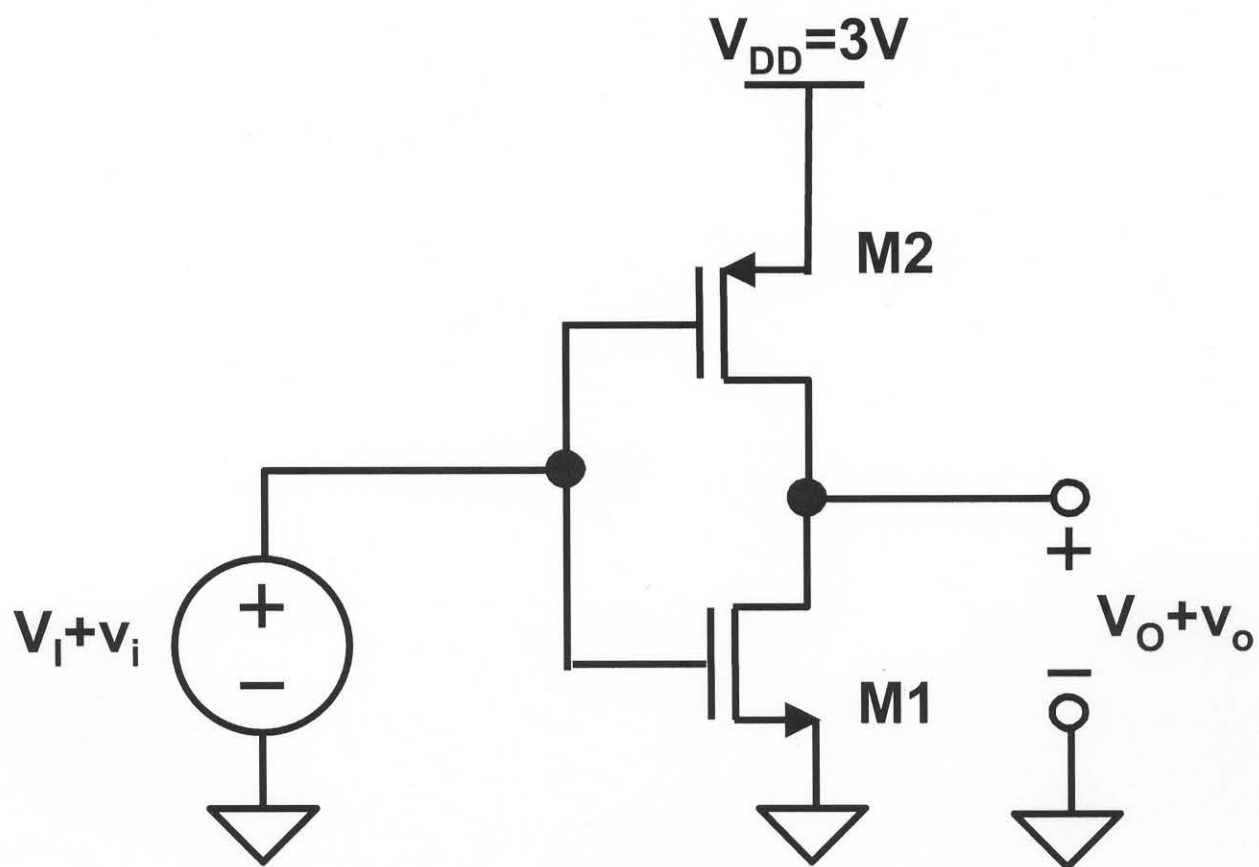
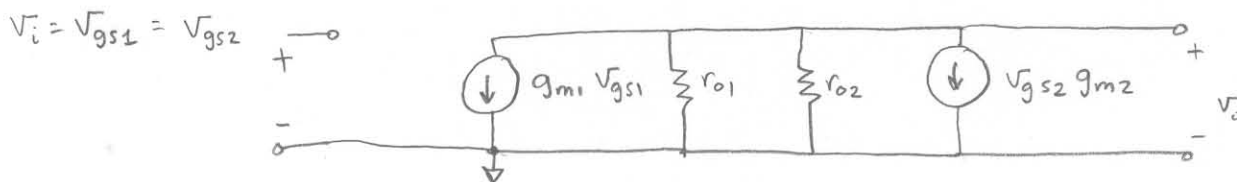


Figure 1: CMOS inverter as linear amplifier.

Problem 1.3 (2 points) Find the small-signal output resistance R_o assuming the bias conditions in Problem 1.1.

Small signal model:



$$r_{o1} = \frac{1}{\lambda I_D} = \frac{1}{(0.1)(75 \mu A)} = 133 \text{ k}\Omega \quad (116 \text{ k}\Omega \text{ for } I_D = 78 \mu A)$$

$$r_{o2} = r_{o1}$$

$$R_{out} = r_{o1} \parallel r_{o2} = \boxed{66.5 \text{ k}\Omega}$$

(58.0) kΩ

Problem 1.4 (3 points) Find the small-signal gain assuming the bias conditions in Problem 1.1.

$$A_v = -G_m R_o = -(g_{m1} + g_{m2})(r_{o1} \parallel r_{o2})$$

$$g_{m1} = K'_n \left(\frac{W}{L}\right)_1 (V_{GS1} - V_{tn}) = (300 \mu A/V^2)(2)(1.5 \text{ V} - 1 \text{ V}) = 300 \mu A/V$$

$$g_{m2} = K'_p \left(\frac{W}{L}\right)_2 (V_{GS2} - V_{tp}) = (100 \mu A/V^2)(6)(1.5 \text{ V} - 1 \text{ V}) = 300 \mu A/V$$

$$\boxed{A_v = -39.9 \approx -40}$$

Problem 1.5 (2 points) Suppose that γ is nonzero and that through source-well biasing, $V_{tn} = 1.25 \text{ V}$ and $V_{tp} = -1.25 \text{ V}$. How does this affect the small-signal gain (assume the bias conditions in Problem 1.1)?

$$A_v = -(g_{m1} + g_{m2})(r_{o1} \parallel r_{o2}) = -\frac{(g_{m1} r_{o1}) r_{o2}}{r_{o1} + r_{o2}} + -\frac{r_{o1} (g_{m2} r_{o2})}{r_{o1} + r_{o2}}$$

$$g_{m1} r_{o1} = \frac{1}{\lambda} \left(\frac{2}{V_{GS1} - V_{t1}} \right) = \left(\frac{1}{0.1} \right) \left(\frac{2}{1.5 - 1} \right) = 40 \quad \text{for } V_{t1} = 1.0, \quad g_{m1} r_{o1} = 80 \quad \text{for } V_{t1} = 1.25$$

$$\boxed{A_v \text{ doubles, } A_v \approx -80}$$

2 Differential Amplifier

Figure 2 shows the circuit schematic for a differential amplifier. For this problem, use the transistor parameters in Table 2. Assume the following circuit parameters: $I_{TAIL} = 590 \mu A$, $R_{TAIL} = 30 \text{ k}\Omega$, $R_1 = 3 \text{ k}\Omega$, $R_2 = 6 \text{ k}\Omega$, $(W/L)_1 = (W/L)_2 = 8$.

Parameter	NMOS	PMOS
V_t	1 V	-1 V
L_d	0	0
X_d	0	0
k'	$300 \mu A/V^2$	$100 \mu A/V^2$
γ	0	0
λ	0	0

Table 2: Problem 2 Transistor Parameters.

Problem 2.1 (3 points) Find V_I such that $V_s = 300 \text{ mV}$.

$$I_1 = I_2 \Rightarrow I_1 = \frac{1}{2} \left(I_{TAIL} + \frac{V_s}{R_{TAIL}} \right) = \frac{1}{2} \left(590 \mu A + \frac{300 \text{ mV}}{30 \text{ k}\Omega} \right) = 300 \mu A$$

$$V_{ov1} = \sqrt{\frac{2I_1}{K'_n(W/L)_1}} = \sqrt{\frac{2(300 \mu A)}{300 \frac{\mu A}{V^2} (8)}} = 0.5 \text{ V}$$

$$V_I = V_s + V_{t1} + V_{ov1} = 0.3 \text{ V} + 1 \text{ V} + 0.5 \text{ V} = \boxed{1.8 \text{ V}}$$

$$\text{For } I_1 = \frac{I_{TAIL}}{2}, V_I = 1.796 \text{ V}$$

Problem 2.2 (3 points) Find $(W/L)_3 = (W/L)_4$ such that $V_O = 1.5 \text{ V}$, assuming the bias conditions you found in Problem 2.1.

$$I_3 = I_4, I_3 = I_1 + \frac{V_O}{R_1 + 2R_2} = 300 \mu A + \frac{1.5 \text{ V}}{3 \text{ k}\Omega + 2(6 \text{ k}\Omega)} = 400 \mu A$$

↑ by symmetry

$$|V_{GS3}| = \left| \frac{2R_2 V_O}{R_1 + 2R_2} - V_{DD} \right| = \left| \frac{12 \text{ k}\Omega}{15 \text{ k}\Omega} 1.5 \text{ V} - 3 \text{ V} \right| = 1.8 \text{ V} \Rightarrow 400 \mu A = \frac{K'_p}{2} \left(\frac{W}{L} \right)_3 (|V_{GS3}| - |V_{tp}|)^2$$

$$\Rightarrow \left(\frac{W}{L} \right)_3 = \frac{(400 \mu A)(2)}{(100 \mu A/V^2)(1.8 - 1)^2} = 12.5 \quad \boxed{\left(\frac{W}{L} \right)_3 = \left(\frac{W}{L} \right)_4 = 12.5} \quad \text{For } I_3 = 295 \mu A, (W/L)_3 = 23.6$$

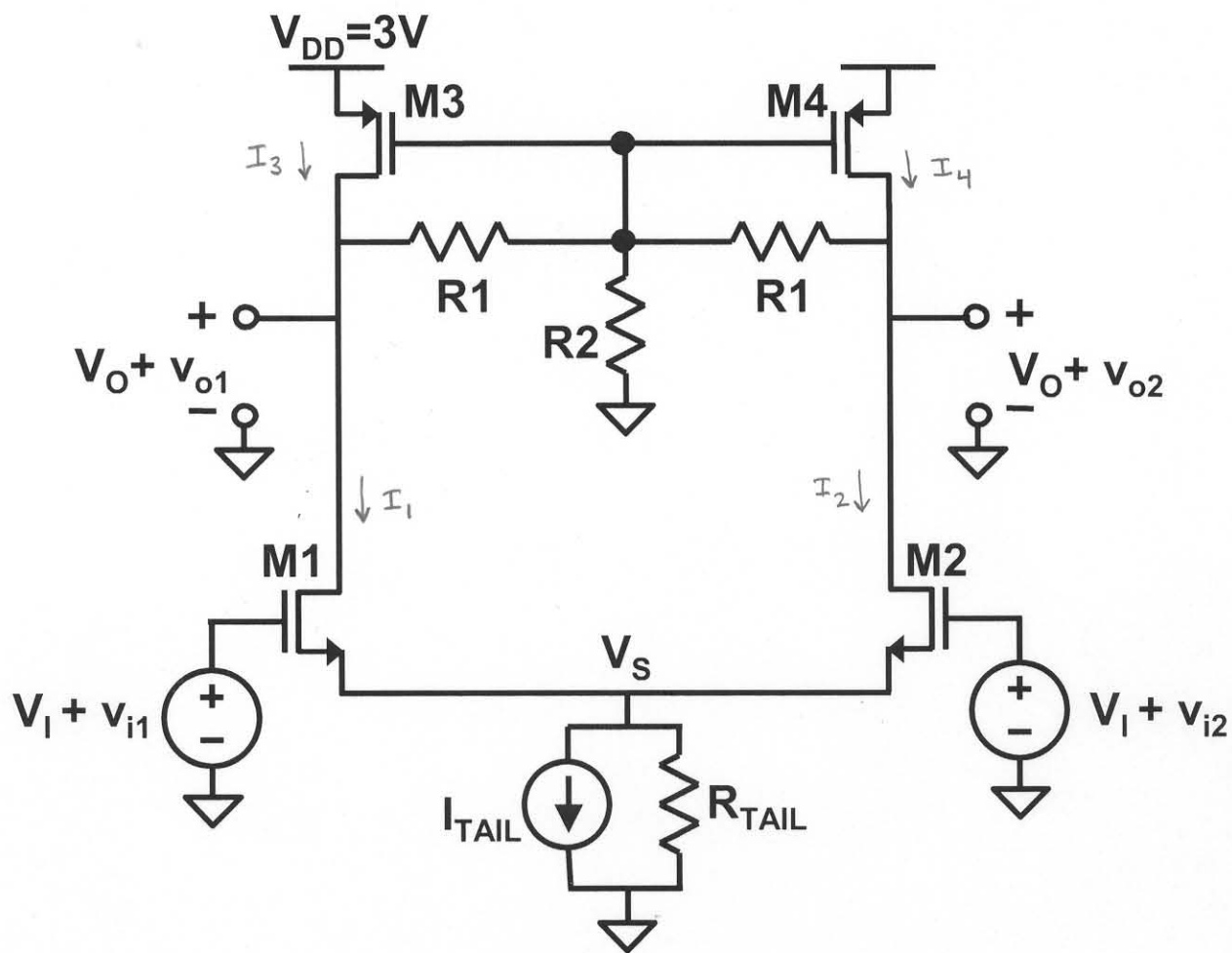
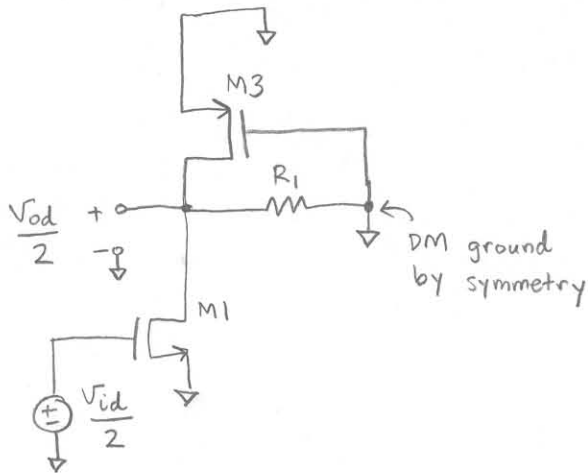


Figure 2: Differential amplifier.

Problem 2.3 (4 points) Draw and label the small-signal differential-mode half circuit, and find the differential-mode gain, $\frac{v_{od}}{v_{id}}$, where $v_{id} = v_{i1} - v_{i2}$ and $v_{od} = v_{o1} - v_{o2}$.



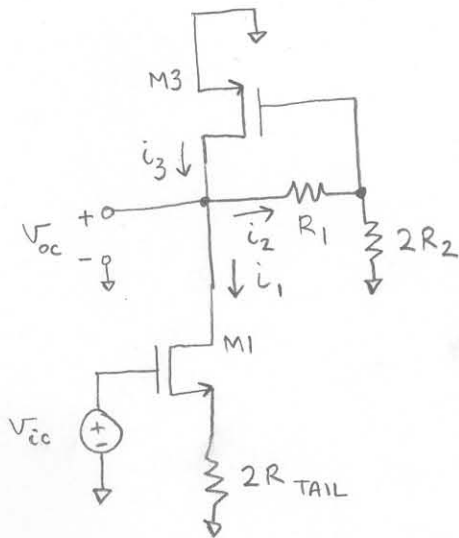
$$g_{m1} = K_n' \left(\frac{W}{L} \right)_1, V_{ov1} = \frac{300 \mu A}{V^2} (8) (0.5 V) = 1200 \mu A/V$$

$$R_o = R_1 = 3 k\Omega$$

$$\frac{v_{od}}{v_{id}} = -(1200 \mu A/V) (3 k\Omega)$$

$$\boxed{\frac{v_{od}}{v_{id}} = -3.6}$$

Problem 2.4 (6 points) Draw and label the small-signal common-mode half circuit, and find the common-mode gain, $\frac{v_{oc}}{v_{ic}}$, where $v_{ic} = 0.5(v_{i1} + v_{i2})$ and $v_{oc} = 0.5(v_{o1} + v_{o2})$.



$$i_1 = g_{m1} (v_{ic} - i_1 2R_{TAIL}) \Rightarrow i_1 = \frac{g_{m1} v_{ic}}{1 + 2R_{TAIL} g_{m1}}$$

$$i_2 = \frac{v_{oc}}{R_1 + 2R_2}$$

$$i_3 = -g_{m3} \left(\frac{2R_2}{2R_2 + R_1} \right) v_{oc}$$

$$i_1 = i_3 - i_2$$

$$i_1 = \frac{1200 \mu A/V (v_{ic})}{1 + 2(30 k\Omega)(1200 \mu A/V)} = (1.64 \times 10^{-5}) v_{ic}$$

$$i_2 = \frac{v_{oc}}{15 k\Omega}$$

$$g_{m3} = K_p' \left(\frac{W}{L} \right)_3, V_{ov3} = 1 mA/V$$

$$i_3 = -\frac{1 mA/V}{5} \cdot 4 v_{oc} = (-8 \times 10^{-4}) v_{oc}$$

$$\frac{v_{oc}}{v_{ic}} = \frac{-1.64 \times 10^{-5}}{(6.67 \times 10^{-5} + 8.0 \times 10^{-4})} \Rightarrow \boxed{\frac{v_{oc}}{v_{ic}} = 0.019}$$

Parameter	NMOS	PMOS
V_t	1 V	-1 V
L_d	0	0
X_d	0	0
k'	$300 \mu\text{A}/\text{V}^2$	$100 \mu\text{A}/\text{V}^2$
γ	0	0
λ	0.1 V^{-1}	0.1 V^{-1}

Table 3: Problem 3 Transistor Parameters.

Problem 3.2 (3 points) Find the minimum output voltage $V_{OUT}(MIN)$.

$$V_{OUT}(\min) = I_O R + V_{OV2} + V_{OV3}$$

$$V_{OV3} = \sqrt{\frac{2I_O}{K_n'(W/L)_3}} = \sqrt{\frac{2(121 \mu\text{A})}{(300 \mu\text{A}/\text{V}^2)(2)}} = 0.635 \text{ V}$$

$$V_{OV2} = \sqrt{\frac{2(121 \mu\text{A})}{(300 \mu\text{A}/\text{V}^2)(20)}} = 0.201 \text{ V}$$

$$I_O R = (121 \mu\text{A})(10 \text{ k}\Omega) = 1.21 \text{ V} \Rightarrow V_{OUT}(\min) = 2.046 \text{ V}$$

Problem 3.3 (3 points) Find the output resistance R_o .

Output branch looks like cascode w/ common-source amp w/ source degeneration:

$$\text{Cascode: } R_o = r_{o3} [1 + g_{m3} R_{o2}] + R_{o2}$$

$$\text{C.S. Amp w/ degeneration: } R_{o2} = R + r_{o2} (1 + g_{m2} R)$$

$$R_{o2} = 1.09 \text{ M}\Omega$$

$$R_o = 35.5 \text{ M}\Omega$$

$$g_{m3} = \sqrt{K_n' 2I_D \left(\frac{W}{L}\right)_3} = 3.81 \times 10^{-4} \text{ A/V}$$

$$g_{m2} = \sqrt{K_n' 2I_D \left(\frac{W}{L}\right)_2} = 1.205 \times 10^{-3} \text{ A/V}$$

$$r_{o2} = r_{o3} = \frac{1}{\lambda I_D} = \frac{1}{(0.1)(121 \mu\text{A})} = 82.65 \text{ k}\Omega$$

$$\text{Or } R_o \approx g_{m3} r_{o3} (g_{m2} r_{o2} R) \approx 31.4 \text{ M}\Omega$$

Problem 3.4 (2 points) Resistor R can be used to model the parasitic resistance associated with routing current sources for long distances on an IC. Find the largest value for R such that I_O is within 1% of the current reference value in Figure 3. Assume $(W/L)_1 = (W/L)_3 = (W/L)_2 = 2$.

$$I_o(\min) = (0.99)(600 \mu A) = 594 \mu A$$

$$I_o(\min) R = V_{ov1} - V_{ov2} \Big|_{I_o(\min)} \Rightarrow R(594 \mu A) = \sqrt{\frac{2(600 \mu A)}{(300 \mu A/\sqrt{2})(2)}} - \sqrt{\frac{2(594 \mu A)}{(300 \mu A/\sqrt{2})(2)}}$$

$$\boxed{R = 119 \Omega}$$

4 Current Source Reference

Figure 4 shows a current reference circuit. For this problem, use the transistor parameters in Table 4. For the circuit in Figure 4, assume the following circuit parameters: $R = 10 \text{ k}\Omega$, $(W/L)_1 = (W/L)_2$, $(W/L)_3 = 2$, and $(W/L)_4 = (W/L)_5 = (W/L)_6 = 6$.

Parameter	NMOS	PMOS
V_t	1 V	-1 V
L_d	0	0
X_d	0	0
k'	$300 \mu\text{A}/\text{V}^2$	$100 \mu\text{A}/\text{V}^2$
γ	0	0
λ	0	0

Table 4: Problem 4 Transistor Parameters.

Problem 4.1 (6 points) Find $(W/L)_1 = (W/L)_2$ and $(W/L)_7$ such that I_O is dependent on process parameters only (i.e., independent of bias point to first order).

$$\text{KVL (bottom): } V_{GS3} + V_R = V_{GS1} + V_{GS2} + (-V_{GS7})$$

$$\begin{aligned} V_R &= \cancel{V_{tn}} + V_{ov1} + V_{tn} + V_{ov2} + |V_{tp}| + |V_{ov7}| - V_{ov3} - \cancel{V_{tn}} \\ &= \underbrace{V_{ov1} + V_{ov2} + |V_{ov7}| - V_{ov3}}_{\substack{\text{bias dependent,} \\ \text{want} = 0}} + \underbrace{V_{tn} + |V_{tp}|}_{\text{process dependent}} \end{aligned}$$

$$\text{Current mirror (top): } (W/L)_4 = (W/L)_5 = (W/L)_6 \Rightarrow I_{REF} = I_2 = I_O$$

$$V_R = \sqrt{\frac{2I_O}{K'_n(W/L)_1}} + \sqrt{\frac{2I_O}{K'_n(W/L)_2}} + \sqrt{\frac{2I_O}{K'_p(W/L)_7}} - \underbrace{\sqrt{\frac{2I_O}{K'_n(2)}}}_{\substack{-\sqrt{\frac{I_O}{K'_n}}}} + 2 \text{ V}$$

$$\text{Choose } (W/L)_1 = (W/L)_2 = 9(W/L)_3$$

$$\text{Choose } (W/L)_7 = \frac{K'_n}{K'_p} \cdot 9(W/L)_3 = 27(W/L)_3$$

$$\Rightarrow V_R = \frac{1}{3} \sqrt{\frac{I_O}{K'_n}} + \frac{1}{3} \sqrt{\frac{I_O}{K'_n}} + \frac{1}{3} \sqrt{\frac{I_O}{K'_n}} - \sqrt{\frac{I_O}{K'_n}} + 2 \text{ V} = 2 \text{ V} \Rightarrow I_O = \frac{V_R}{R} = \frac{2 \text{ V}}{10 \text{ k}\Omega}$$

$$\boxed{I_O = 200 \mu\text{A}}$$

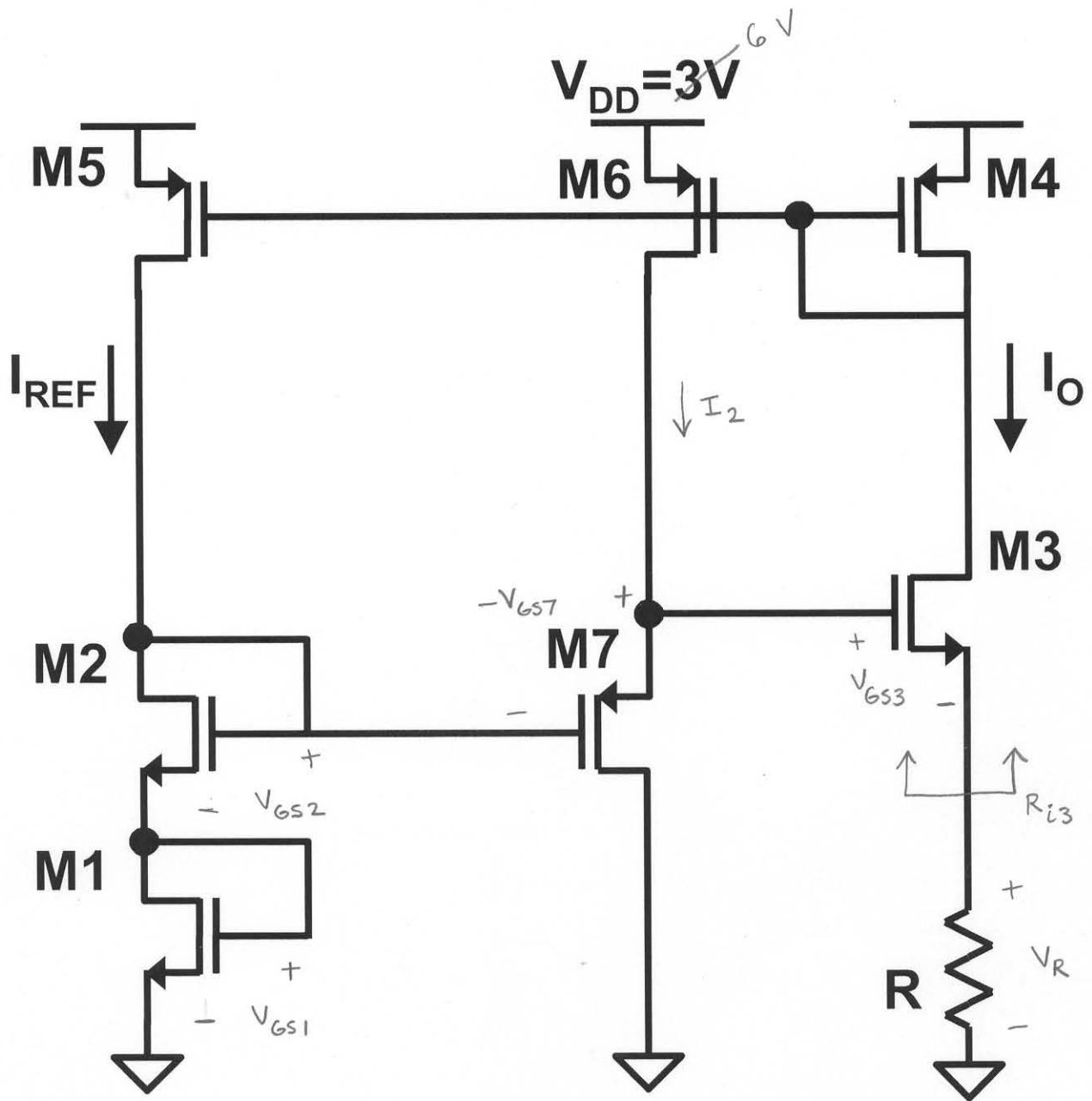


Figure 4: Current source reference.

Problem 4.2 (6 points) One can model the thermal noise of resistor R as a small-signal current source i_n in parallel with R . Quantify the impact of the noise current source on the total output current $I_O + i_o$, assuming the bias point you found in Problem 4.1 and $|i_n| = 1\mu\text{A}$.

Small-signal model:



Current gain for common-gate: $\frac{i_o}{i_i} = 1$

$R_{i3} \equiv$ common-gate input resistance
 $= \frac{1}{g_{m3}} \quad (\lambda=0)$

$$\frac{i_i}{i_n} = \frac{R}{R + R_{i3}} \quad (\text{current divider})$$

$$\Rightarrow \frac{i_o}{i_n} = (1) \frac{R}{R + 1/g_{m3}}$$

$$\begin{aligned} g_{m3} &= \sqrt{2 I_O K_n' \left(\frac{W}{L}\right)_3} \\ &= \sqrt{2 (200\mu\text{A}) \left(\frac{300\mu\text{A}}{\sqrt{2}}\right) (2)} \\ &= 4.90 \times 10^{-4} \text{ S} \end{aligned}$$

$$\frac{i_o}{i_n} = \frac{10 \text{ k}\Omega}{10 \text{ k}\Omega + 2.04 \text{ k}\Omega} = 0.83 \Rightarrow |i_o| = 0.83 \mu\text{A}$$

$$\boxed{\frac{|i_o|}{|I_O|} = 0.415 \%}$$